

| L Number | Hits | Search Text  | DB  | Time stamp          |
|----------|------|--|---|---------------------|
| 1        | 37   | 438/257,366,367,368,369,303.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/07<br>09:10 |
| 2        | 37   | 438/257,366,367,368,369,303.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/07<br>09:10 |
| 3        | 1    | 438/257,366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and gate and (gate adj dielectric)           | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/07<br>09:14 |
| 4        | 0    | 438/257.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack) and (non-volatile adj memory adj stack) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/07<br>09:18 |
| 5        | 0    | 438/257.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack) and (non-volatile adj memory adj stack)           | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/07<br>09:19 |
| 6        | 0    | 438/257.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (spacer\$2) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack) and (non-volatile adj memory adj stack)         | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/07<br>09:19 |
| -        | 1    | 6753242.pn. and (electrode adj region)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:23 |
| -        | 50   | gate adj electrode and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (nitride adj spacers) and (channel adj region)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/08/31<br>13:42 |
| -        | 36   | gate adj electrode and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (nitride adj spacers) and (channel adj region) and @ad<20020319   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/08/31<br>14:17 |
| -        | 36   | gate adj electrode and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (nitride adj spacers) and (channel adj region) and @ad<20020319   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/08/31<br>14:41 |
| -        | 1    | 20020028541.pn. and (nitride adj layer) and (oxide adj layer)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/08/31<br>14:36 |
| -        | 1    | 20020028541.pn. and (nitride adj spacer) and (oxide adj spacer)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/08/31<br>14:36 |

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| - | 13 | gate adj electrode and (semiconductor adj substrate) and dielectric and source and drain and ((oxide adj spacers) same (nitride adj spacers)) and (channel adj region) and @ad<20020319  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>10:36 |
| - | 1  | (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>10:39 |
| - | 0  | (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack) and (non-volatile adj memory adj stack)         | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/07<br>09:17 |
| - | 1  | (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>10:41 |
| - | 1  | (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>11:38 |
| - | 1  | 6596599.pn. and ((anti-reflective adj coating) or (ARC))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>12:08 |
| - | 3  | (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and gate and (gate adj dielectric)                                   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>12:27 |
| - | 1  | 6117719.pn. and ((anti-reflective adj coating) or (ARC))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>12:10 |
| - | 1  | 6207482.pn. and ((anti-reflective adj coating) or (ARC))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>12:10 |
| - | 2  | 438/595,696,230,778-785.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and gate and (gate adj dielectric) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>10:38 |
| - | 1  | 438/366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and gate and (gate adj dielectric)     | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/07<br>09:14 |
| - | 1  | 438/366,367,368,369,303.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and gate and (gate adj dielectric) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>10:37 |

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| - | 2 | 5902125.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>14:40 |
| - | 2 | 5960270.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>14:43 |
| - | 2 | 5972762.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>14:44 |
| - | 0 | 6066567pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>14:44 |
| - | 2 | 6066567.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>14:45 |
| - | 2 | 6087271.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>14:50 |
| - | 2 | 6156126.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>14:50 |
| - | 2 | 6245682.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>14:51 |
| - | 2 | 6368947.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>14:51 |
| - | 0 | (gate adj electrode) and (semiconductor<br>adj substrate) and dielectric and source<br>and drain and (dielectric adj spacers)<br>and (channel adj region) and @ad<20020319<br>and (anti-reflective adj coating or ARC)<br>and (gate adj stack) and (non-volatile<br>adj memory adj stack) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>09:49 |
| - | 2 | (anti-reflective adj coating or ARC) and<br>(gate adj stack) and (non-volatile adj<br>memory adj stack)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>15:23 |
| - | 2 | 6753242.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/01<br>15:23 |
| - | 2 | 6066567.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>15:34 |
| - | 2 | 5902125.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>15:36 |
| - | 3 | 597262.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>15:37 |
| - | 2 | 6087271.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>15:55 |
| - | 2 | 6555397.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>15:57 |

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| - | 1 | 20000816.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>16:00 |
| - | 0 | 20000814.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>16:35 |
| - | 2 | 6136636.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>09:34 |
| - | 2 | 61177743.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>16:57 |
| - | 2 | 6372589.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:24 |
| - | 2 | 6368947.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:25 |
| - | 2 | 6245682.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:25 |
| - | 2 | 6156126.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:26 |
| - | 2 | 6097271.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:27 |
| - | 2 | 6087271.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:27 |
| - | 2 | 6066567.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:28 |
| - | 2 | 5972762.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:28 |
| - | 2 | 5960270.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:30 |
| - | 2 | 5902125.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:31 |
| - | 2 | 438/595,696,230,778-785.ccls. and (gate<br>adj electrode) and (semiconductor adj<br>substrate) and dielectric and source and<br>drain and (oxide adj spacers) and<br>(channel adj region) and @ad<20020319 and<br>(anti-reflective adj coating or ARC)         | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:34 |
| - | 1 | 438/366,367,368,369.ccls. and (gate adj<br>electrode) and (semiconductor adj<br>substrate) and dielectric and source and<br>drain and (oxide adj spacers) and<br>(channel adj region) and @ad<20020319 and<br>(anti-reflective adj coating or ARC) and<br>gate | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/02<br>17:34 |

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| - | 0   | 6136636.pn. and non-volatile  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>09:36 |
| - | 0   | 6136636.pn. and memory  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>09:38 |
| - | 0   | 6136636.pn. and floating  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>09:38 |
| - | 0   | @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack) and (non-volatile adj memory adj stack)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>09:50 |
| - | 0   | @ad<20020319 and (anti-reflective adj coating or ARC) and ((gate adj stack) or (transistor)) and (non-volatile adj memory adj stack)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>09:53 |
| - | 0   | @ad<20020319 and ((anti-reflective adj coating) or (ARC or BARC)) and ((gate adj stack) or (transistor)) and (non-volatile adj memory adj stack)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>09:55 |
| - | 350 | @ad<20020319 and ((anti-reflective adj coating) or (ARC or BARC)) and ((gate adj stack) or (transistor)) and (non-volatile adj memory)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>09:56 |
| - | 48  | @ad<20020319 and ((anti-reflective adj coating) or (ARC)) and ((gate adj stack) or (gate adj transistor)) and (non-volatile adj memory)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>10:02 |
| - | 13  | @ad<20020319 and ((anti-reflective adj coating) or (ARC)) and ((gate adj stack) or (gate adj transistor)) and (non-volatile adj memory) and spacers   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/03<br>10:02 |
| - | 1   | 438/366,367,368,369,303.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/06<br>17:24 |
| - | 2   | 438/595,696,230,778-785.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/06<br>17:24 |
| - | 19  | 438/366,367,368,369,303.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/07<br>09:10 |
| - | 22  | 438/595,696,230,778-785.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/09/06<br>17:24 |